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# FDN359AN N-Channel Logic Level PowerTrench™ MOSFET

#### **General Description**

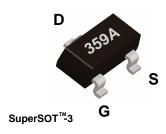
This N-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

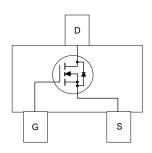
These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

#### **Features**

- Very fast switching.
- Low gate charge (5nC typical).
- High power version of industry standard SOT-23 package. Identical pin out to SOT-23 with 30% higher power handling capability.







### **Absolute Maximum Ratings** $T_A = 25^{\circ}\text{C}$ unless other wise noted

Symbol	Parameter	Ratings	Units	
V <sub>DSS</sub>	Drain-Source Voltage	30	V	
/ <sub>GSS</sub>	Gate-Source Voltage	±20	V	
)	Maximum Drain Current - Continuous (Note 1a)	2.7	А	
	- Pulsed	15		
$P_{D}$	Maximum Power Dissipation (Note 1a)	0.5	W	
	(Note 1b)	0.46		
J,T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to 150	°C	
HERMA	L CHARACTERISTICS			
R <sub>OJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1a)	250	°C/W	
₹ <sub>⊌C</sub>	Thermal Resistance, Junction-to-Case (Note 1)	75	°C/W	

Symbol	Parameter	Conditions		Min	Тур	Max	Units
OFF CHAR	ACTERISTICS	·					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		30			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	I <sub>D</sub> =250 μA, Referenced to 25 °C			23		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, \ V_{GS} = 0 \text{ V}$				1	μA
			T <sub>J</sub> = 55°C			10	μΑ
I <sub>GSSF</sub>	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	•			100	nA
I <sub>GSSR</sub>	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
ON CHARAC	CTERISTICS (Note)			•		,	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		1	1.6	3	V
$\Delta V_{GS(th)}/\Delta T_{J}$	Gate Threshold Voltage Temp. Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25 °C			-4		mV/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 2.7 \text{ A}$			0.037	0.046	Ω
, ,			T <sub>J</sub> =125°C		0.055	0.075	
		$V_{GS} = 4.5 \text{ V}, I_D = 2.4 \text{ A}$			0.049	0.06	
I <sub>D(ON)</sub>	On-State Drain Current	$V_{GS} = 10 \text{ V}, \ V_{DS} = 5 \text{ V}$		15			Α
<b>g</b> <sub>FS</sub>	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 2.7 \text{ A}$			9.5		S
DYNAMIC C	HARACTERISTICS						
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz			480		pF
C <sub>oss</sub>	Output Capacitance				120		pF
C <sub>rss</sub>	Reverse Transfer Capacitance				45		pF
SWITCHING	CHARACTERISTICS (Note)						
t <sub>D(on)</sub>	Turn - On Delay Time	$V_{DD} = 5 \text{ V}, \ I_D = 1 \text{ A},$ $V_{GS} = 4.5 \text{ V}, \ R_{GEN} = 6 \Omega$			6	12	ns
ţ,	Turn - On Rise Time				13	24	ns
$t_{D(off)}$	Turn - Off Delay Time				15	27	ns
t <sub>f</sub>	Turn - Off Fall Time				4	10	ns
$Q_g$	Total Gate Charge	$V_{DS} = 10 \text{ V}, \ I_{D} = 2.7 \text{ A}, \ V_{GS} = 5 \text{ V}$			5	7	nC
$Q_{gs}$	Gate-Source Charge				1.4		nC
$Q_{gd}$	Gate-Drain Charge				1.6		nC
DRAIN-SOL	IRCE DIODE CHARACTERISTICS AND MA	XXIMUM RATINGS					
l <sub>s</sub>	Maximum Continuous Drain-Source Diode Fo	de Forward Current				0.42	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \ I_{S} = 0.42 \text{ A} \ \text{(Note)}$			0.65	1.2	V

Note:

Typical  $\rm R_{\rm BJA}$  using the board layouts shown below on FR-4 PCB in a still air environment :



a. 250°C/W when mounted on a 0.02 in² pad of 2oz Cu.



b. 270°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2.0%.

<sup>1.</sup>  $R_{aux}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{auc}$  is guaranteed by design while  $R_{acx}$  is determined by the user's board design.

## **Typical Electrical Characteristics**

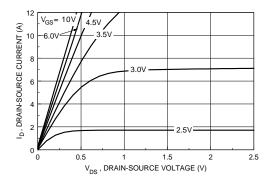


Figure 1. On-Region Characteristics.

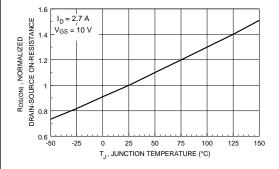


Figure 3. On-Resistance Variation with Temperature.

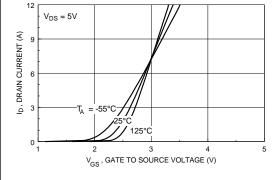


Figure 5. Transfer Characteristics.

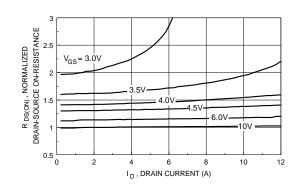


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

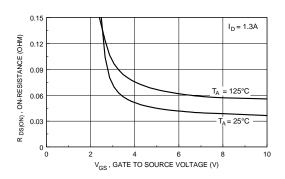


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

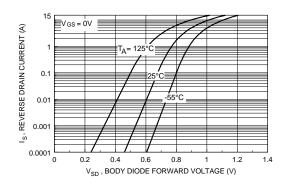


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# **Typical Electrical Characteristics**

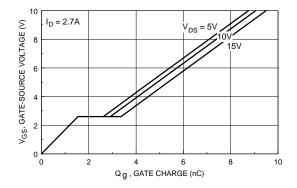


Figure 7. Gate Charge Characteristics.

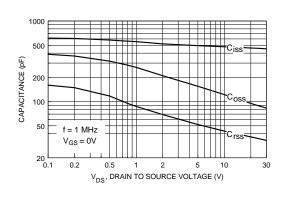


Figure 8. Capacitance Characteristics.

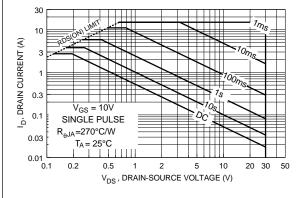


Figure 9. Maximum Safe Operating Area.

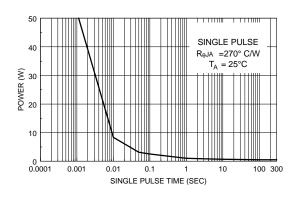


Figure 10. Single Pulse Maximum Power Dissipation.

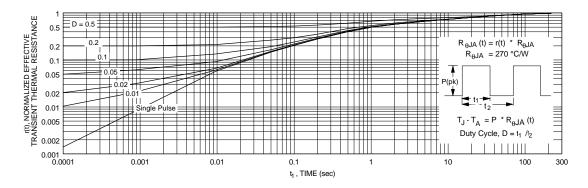


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in note 1b. Transient thermal response will change depending on the circuit board design.

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